

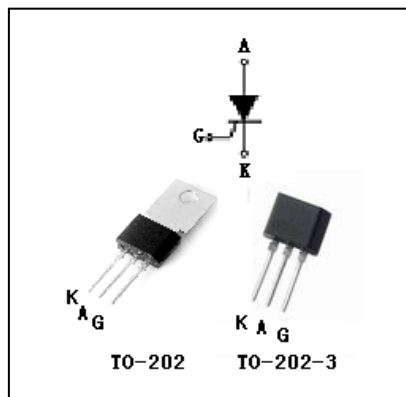
2P6M SCR_s

●Package

T0-202/T0-202-3

●Main Feature(T_j=25℃)

Symbol	Value	Unit
$I_{T(AV)}$	2	A
V_{DRM} / V_{RRM}	≥ 600	V
I_{GT}	200	uA



●Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
$I_T(RMS)$	RMS on-state current (180° conduction angle)	3	A
$I_{T(AV)}$	AV on-state current (180° conduction angle)	2	A
I_{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	20	A
IGM	Peak gate current(tp=20us)	1	A
PGM	Peak gate power	0.5	W
PG(AV)	Average gate power	0.1	W
Tstg	Storage temperature	-40--+150	℃
Tj	Operating junction temperature	-40--+110	℃

●Thermai Resistances

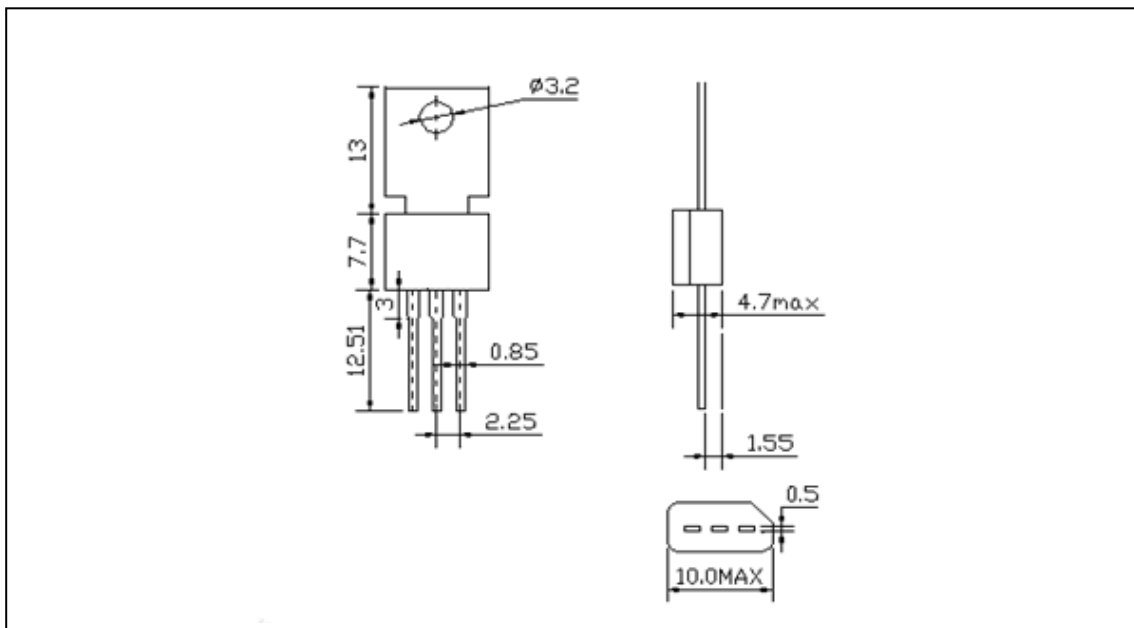
Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case	60	℃/W
Rth (j-a)	Junction to ambient	150	℃/W

● **Electrical characteristics (T_j=25℃ unless otherwise stated)**

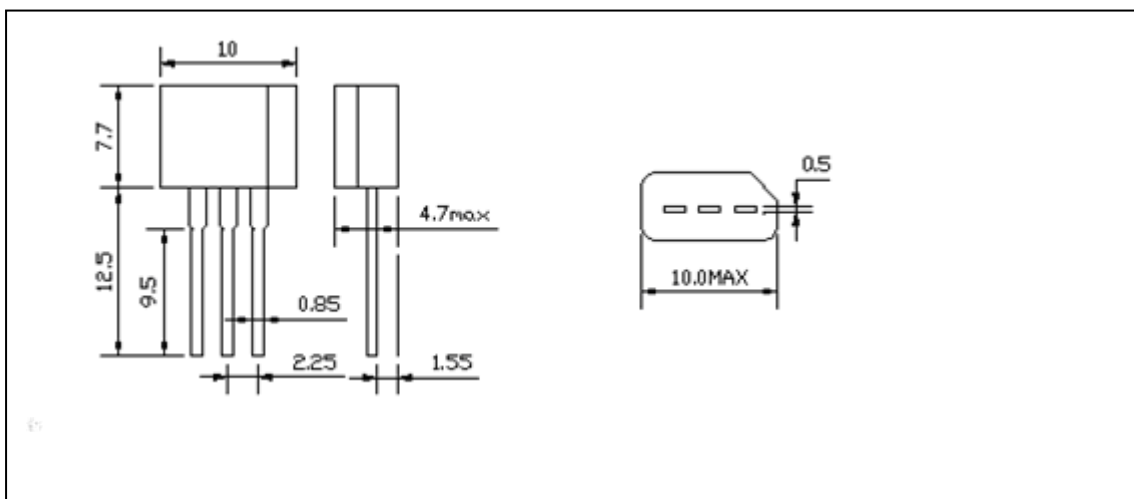
Symbol	Test Conditions		Value			Unit
			Min	Type	Max	
IGT	VD=6V, RL=100 Ω, RGK=1K Ω		-----	-----	200	uA
VGT	VD=12V, RL=100 Ω, RGK=1K Ω		-----	-----	0.8	V
VGD	VD=1/2V _{DRM} , RGK=1K Ω T _j =125℃		0.2	-----	-----	V
IH	VD=24V, RGK=1K Ω, ITM=4A		-----	1	3	mA
dV/dt	VD=2/3V _{DRM} , RGK=1K Ω, T _j =125℃		10	10 [#]	-----	v/ μ s
VTM	ITM=4A		-----	-----	2.2	V
I _{DRM}	VD=V _{DRM}	T _j =125℃	-----	-----	100	uA
I _{RRM}	VR=V _{RRM}	T _j =125℃	-----	-----	100	uA

● Measure of package

(TO-202)



(TO-202-3)



●Electrocircuit:

